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# Effect of Bi<sub>2</sub>O<sub>3</sub> addition on the sintering and microstructural development of gadolinia-doped ceria ceramics

V. Gil\*, J. Tartaj, C. Moure, P. Duran

Instituto de Cerámica y Vidrio (CSIC), Departamento de Electrocerámica, C/Kelsen 5, Cantoblanco 28049, Madrid, Spain Available online 22 May 2006

#### **Abstract**

The effect of small amounts (0.2–2.0 wt.%) of bismuth oxide on the sintering behavior and microstructural development of  $Ce_{0.9}Gd_{0.1}O_{1.95}$  (GDC) submicronized powders has been studied using XRD for the lattice parameter measurements, the constant heating rate (CHR) method in air to monitor the shrinkage kinetics of powder compacts, and scanning electron microscopy (SEM) to study the microstructure of the sintered samples. Sintering of GDC compacts was significantly improved by adding small amounts of  $Bi_2O_3$  ( $\leq 2.0$  wt.%), and samples of doped-GDC sintered at  $1200-1400\,^{\circ}\text{C}$  for 2–4 h were dense bodies (98–99.5% of theoretical density). Measurements showed that the addition of  $Bi_2O_3$  could reduce the sintering temperature by about  $250-300\,^{\circ}\text{C}$  lower than that for undoped-GDC samples. A liquid phase-assisting mechanism was assumed as the main cause for the enhancement of the densification process. The average grain size of doped-GDC sintered samples grew with the increasing of  $Bi_2O_3$  addition up to 1.0 wt.%, and then decreased indicating a poor wetting properties of the formed liquid phase. © 2006 Elsevier Ltd. All rights reserved.

Keywords: Sintering; Grain growth; Microstructure-final; Electrical conductivity; Bi<sub>2</sub>O<sub>3</sub> doped ceria

## 1. Introduction

Although YSZ (yttria stabilized zirconia with 8 mol% Y<sub>2</sub>O<sub>3</sub>) represents the state of the art electrolyte for high temperature (800–1000 °C) solid oxide fuel cells (SOFCs), but many problems related to the correct use of the other components (anode, cathode, and interconnector) of the SOFC are to be present during service at the above operating conditions. Therefore, a lower operating temperature becomes necessary to overcome several difficulties. Being the electrolyte the most important component of the SOFC, many efforts are addressed to the search of new ionic conductor ceramics having a high ionic conductivity within the 500–700 °C temperature range. Ceria-based materials are chosen as the best electrolyte candidate for these operating conditions. They have an ionic conductivity much higher that YSZ at intermediate temperature, but these ceramics requires sintering temperatures in the range of 1300-1600 °C to full density<sup>2-5</sup> leading, thus, to microstructures with a grain size too large and, therefore, with very poor mechanical properties. Although many attempts to lower the sintering temperature of the ceria-based ceramics have been carried out in the last decade,

the use of transition metal oxide seems to be the most effective additive in reducing this. However they introduce some electronic conduction, which can detrimentally affect the oxide-ion conductivity.  $^{6-9}$  Recently Zhang et al.  $^{10-12}$  proposed the use of Fe<sub>2</sub>O<sub>3</sub> as a good sintering promoter for ceria-based ceramics, and Yoshida et al.  $^{13}$  and more recently Lee et al.  $^{14}$  studied the effect of galia additions on the sintering behavior of samaria doped- and gadolinia-doped-ceria, respectively. It is surprising to note that there are not any reports in the literature concerning the densification of commercial gadolinia-doped ceria powders by using Bi<sub>2</sub>O<sub>3</sub> as a sintering promoter.

The aim of the present paper is to study the effect of different doping levels of Bi<sub>2</sub>O<sub>3</sub>, at our best knowledge for the first time, on the sintering behavior and microstructural development of gadolinia-doped ceria (GDC) submicronized powders, leading to establish the minimal doping level required to optimize both sintering and microstructure of the Bi<sub>2</sub>O<sub>3</sub>-doped GDC ceramics.

## 2. Experimental procedure

Commercial gadolinia-doped ceria  $Ce_{0.9}Gd_{0.1}O_{1.95}$  powders (Rhodia GmbH, FRG) with an average particle size of 0.38  $\mu$ m and specific surface of 12.4 m<sup>2</sup>/g, was used as starting raw material, which is referred to as GDC powder thereafter. The dopant,

<sup>\*</sup> Corresponding author. Tel.: +34 917355840; fax: +34 917355843. E-mail address: vanesa@icv.csic.es (V. Gil).

in the form of bismuth nitrate dissolved in ethanol, was added to a GDC/ethanol suspension by stirring. After drying at  $120\,^{\circ}\text{C}$  for 2 h, the powders were calcined at  $700\,^{\circ}\text{C}$  for 2 h, granulated and isopressed at  $200\,\text{MPa}$ . After compaction the green density of the powder compacts was in the order of 50% theoretical density. Sintering was performed in air at a constant heating rate (CHR) of  $2\,^{\circ}\text{C/min}$  up to  $1600\,^{\circ}\text{C}$  in a Netzsch dilatometer (model 407/E of Geratebau, Selb.Bayern, Germany). The samples were also isothermally sintered in air at  $1400\,^{\circ}\text{C}$ , which was held for times from 0 to 8 h.

The density of the sintered samples was measured by the Archimedes method in water. In order to study the possible influence of the  $Bi_2O_3$  additive on the crystalline structure of the prepared samples these were, after calcining, heat-treated at  $1200{-}1400\,^{\circ}\text{C}$  for 2 h, milled in an agate mortar, and then characterized by X-ray diffraction (XRD) with a Siemens diffractometer (model D-5000, Erlangen, Germany) using nickel-filtered Cu K $\alpha$  radiation ( $\lambda$  = 0.15405 nm). An internal standard was used for the lattice parameter measurements. Besides this, a powder mixture containing GDC and  $Bi_2O_3$  50/50 in wt.% was homogenized and heat-treated for several hours at 850–1200 °C for 2 h. The new formed phases, if any, were also investigated by XRD.

The microstructure of the sintered samples was examined in a Zeiss (SEM) scanning electron microscope (model DSM 950, Oberkochem, Germany). The average grain size was measured by the intercept method on the surface of polished and thermally etched sintered samples. The size of at least 300 grains was taken into account.

#### 3. Results and discussions

### 3.1. X-ray diffraction study

The XRD study carried out on the doped-GDC samples sintered in the temperature range of  $1200-1400\,^{\circ}\text{C}$ , as it is shown in Fig. 1, did not show the presence of free Bi<sub>2</sub>O<sub>3</sub> or secondary

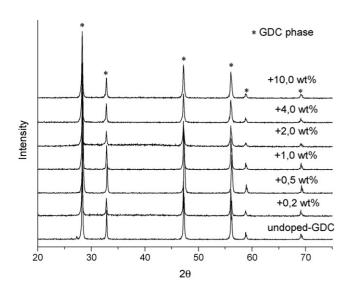


Fig. 1. XRD patterns of doped-GDC powders and undoped after heat-treatment at  $1200\,^{\circ}\text{C}$  for 2 h.

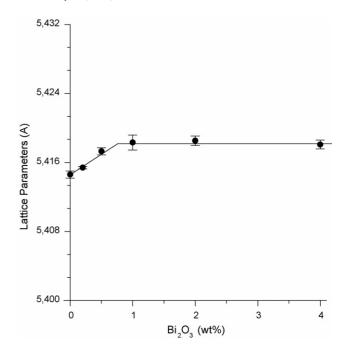


Fig. 2. Lattice parameter of the GDC-Bi $_2$ O $_3$  composites (1400  $^{\circ}$ C-2 h) as a function of the Bi $_2$ O $_3$  content.

peak phases, i.e. if some new phases were formed, the amounts was too small to be detected by X-ray diffraction.

However the XRD peaks for doped-GDC samples were slightly shifted to smaller angles with increasing  $Bi_2O_3$  content up to about 1.0 wt.%, but with  $Bi_2O_3$  additions above that concentration the peaks were not shifted further. The shift to smaller angles indicates that the lattice constant is increased when  $Bi_2O_3$  is added to the GDC samples. Such an increase in the lattice constants can be considered as to be due to the substi-

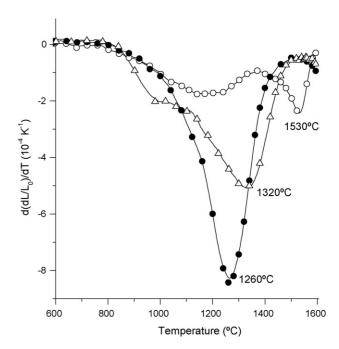


Fig. 3. Effect of sintering temperature on shrinkage rate for: ( $\bigcirc$ ) undoped-GDC, ( $\triangle$ ) +0.5 wt.% Bi<sub>2</sub>O<sub>3</sub> and ( $\blacksquare$ ) +2.0 wt.% Bi<sub>2</sub>O<sub>3</sub>.

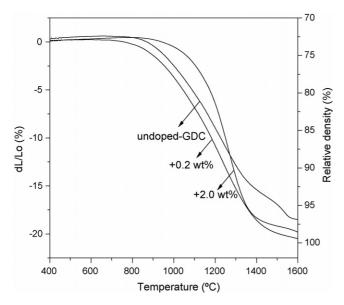


Fig. 4. Effect of sintering temperature on linear shrinkage.

tution of larger Bi<sup>3+</sup> ions (0.117 nm) for the smaller Ce<sup>4+</sup> ions (0.097 nm) in the GDC structure. Such substitution reaction can be described, taking into account the Kröger-Vink notation, by the following equation:

$$Bi_2O_3 \xrightarrow{CeO_2} 2Bi'_{ce} + V''_O + 3O^x_O$$

From that equation the formation of oxygen vacancies because of charge compensation should be assumed.

Therefore, from the above results we can estimate that  $Bi_2O_3$  dissolves in the GDC structure, as shown in Fig. 2, for about 0.8 wt.%  $Bi_2O_3$  addition.

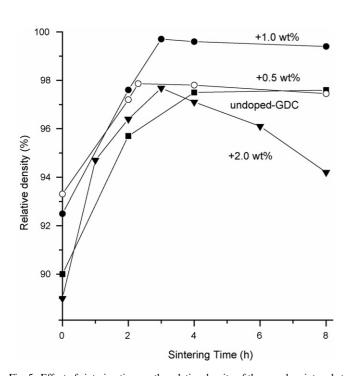


Fig. 5. Effect of sintering time on the relative density of the samples sintered at 1400  $^{\circ}\text{C}.$ 

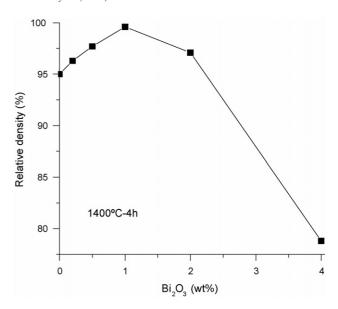


Fig. 6. Sintered density as a function of Bi<sub>2</sub>O<sub>3</sub> content.

# 3.2. Non-isothermal sintering

The sintering behavior of GDC powders doped with different amounts of  $Bi_2O_3$  is shown in Figs. 3 and 4. The shrinkage rate spectra  $d(dL/L_0)/dT$  (Fig. 3) and the relative density (Fig. 4) are plotted as a function of temperature for different bismuth oxide concentration. The curve for 1.0 wt.%  $Bi_2O_3$ -doped GDC sample in Fig. 3 exhibits a similar shrinkage trend to that of 0.5 wt.%  $Bi_2O_3$ -doped GDC and, for clarity, it has been omitted. As it can be seen, the  $Bi_2O_3$  doping is quite effective in enhancing the densification of GDC when its content was  $\geq 0.5$  wt.%, and it is clear from that figure that the maximum shrinkage rate strongly

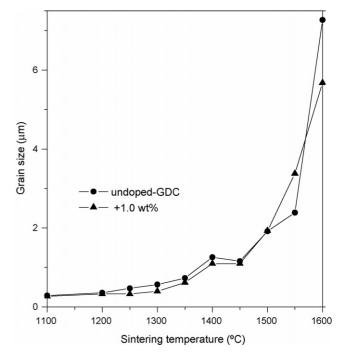


Fig. 7. Grain size as a function of sintering temperature for undoped-GDC and 1.0 wt.% Bi<sub>2</sub>O<sub>3</sub>-doped GDC samples.

increases with increasing  $\rm Bi_2O_3$  content and, for example, a doping of GDC sample with 2.0 wt.%, this was a factor of 2–5 higher compared to undoped-GDC ones. From Fig. 4, it can be observed that the undoped-GDC samples do not reached its final shrinkage below 1600 °C with a shrinkage of about 18%, while the samples containing 0.2 wt.%  $\rm Bi_2O_3$  reached its final shrinkage at about 1450 °C and a shrinkage of 21%. From that figure, it is also clear that the  $T_{\rm s}$ , i.e. the temperature at which the relative density of the sintered sample attains 95% of theoretical density, decrease from about 1580 to 1370 °C, i.e. more than 200 °C with the only addition of 0.2 wt.%  $\rm Bi_2O_3$ . It must be mentioned that

all samples reached 96–99% of theoretical density at the end of the non-isothermal sintering process at 1600 °C.

# 3.3. Isothermal sintering

The effect of the  $\mathrm{Bi}_2\mathrm{O}_3$  additions in enhancing the densification of GDC ceramics was also evidenced by studying the evolution of the density of the samples as a function of the sintering time. As it is shown in Fig. 5, the density of the undoped-GDC samples monotonically increase with increasing sintering time, reaching a density of 97.6% after sintering

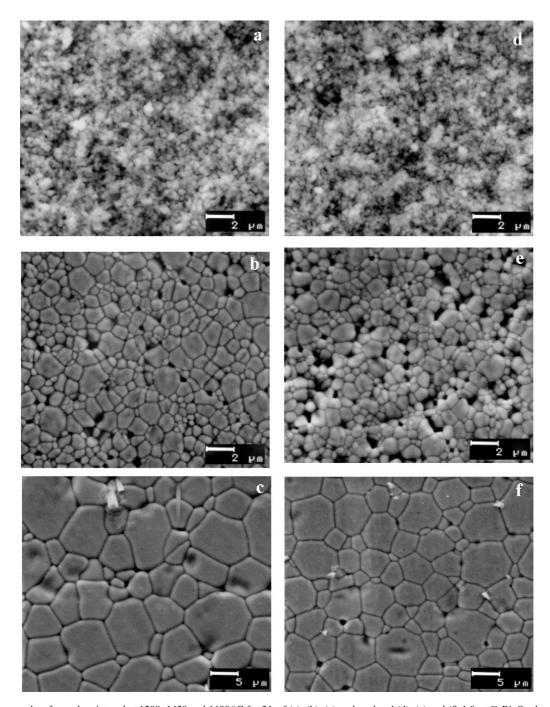


Fig. 8. SEM micrographs of samples sintered at 1200, 1450 and 1600  $^{\circ}$ C for 2 h of (a), (b), (c) undoped and (d), (e) and (f) 1.0 wt.% Bi<sub>2</sub>O<sub>3</sub>-doped GDC samples, respectively.

at 1400 °C for 8 h. However, the doped-GDC samples attain a density as high as 97.9 and 99.7% of theoretical density after sintering time of about 2 and 3 h for the samples containing 0.5 and 1.0 wt.% Bi<sub>2</sub>O<sub>3</sub>, respectively. As it can be seen, for higher sintering time the density of the doped-GDC samples slightly decreased, which indicates that although the addition of small amounts of Bi<sub>2</sub>O<sub>3</sub> to GDC powders strongly enhances the sintering behavior of these ceramics, but its density decreased when the sintering temperatures are relatively high (>1350–1400 °C), and/or the sintering time is too long (>2-3 h). This fact is particularly clear when the Bi<sub>2</sub>O<sub>3</sub> content is 2.0 wt.%. Fig. 6 shows the sintered density of GDC samples as a function of Bi<sub>2</sub>O<sub>3</sub> content and, it is shown that the sintered density increases with increasing Bi<sub>2</sub>O<sub>3</sub> up to 1.0 wt.%. For higher Bi<sub>2</sub>O<sub>3</sub> concentration, the sintered density rapidly deteriorated as shown in such a figure, i.e. a dedensification phenomenon is present<sup>15</sup> which can be attributed, in principle, to both the evaporation of Bi<sub>2</sub>O<sub>3</sub> and the release of oxygen gas from some reduction of CeO<sub>2</sub> to  $Ce_2O_3$ , according to the following equation:

$$2\text{CeO}_2 \rightarrow \text{Ce}_2\text{O}_3 + \frac{1}{2}\text{O}_2$$

From all the above, it could be assumed that an optimal amount of  $Bi_2O_3$  to be used as an aid for sintering of GDC ceramics is 1.0 wt.%. In the same way, an optimized sintering temperature could be located in the 1350–1400 °C range, which can be considered as a competitive temperature for a co-sintering process.

### 3.4. Microstructural development

Taking into account the above results, a study of the evolution of the grain size as a function of the temperature was carried out only on the doped-GDC samples containing 1.0 wt. % Bi<sub>2</sub>O<sub>3</sub>, as shown in Fig. 7. For comparison, the evolution of the grain size in the undoped-GDC samples is also shown. As it can be seen, there is a first region up to 1200 °C, the sample was only 87% dense and with open porosity, in which the grain size is hardly affected by the presence of the additive. It can be associated with the early stage-sintering 16 and, on the other hand, the wetting properties of the formed liquid phase are, probably, very poor at that temperature impeding, thus, the diffusion of some material. A second region, above 1200 °C and up to 1400 °C in which a little grain growth but with a homogeneous grain size took place. 17,18 At this temperature range, the viscosity of the liquid phase will be much lower than that at 1200 °C, and the grain size monotonically increases with increasing temperature. This evolution of the grain size could be related with the intermediatestage sintering, i.e. in which the samples are >95% dense and closed porosity. In the undoped-GDC samples the grain size increases with increasing temperature up to 1400 °C, according to a sintering process dominated by a solid-state diffusion mechanism. <sup>19</sup> Above 1400 °C, i.e. at the last-stage sintering, the grain growth in both kinds of samples was much faster than in the second region and, according to the suggestions of Kingery et al., <sup>20</sup> a rapid grain growth by a solid-state reaction mechanism

took place. Fig. 8 shows the SEM micrographs corresponding to these samples sintered at different temperatures.

#### 4. Conclusions

From the above experimental described results, we can state the following: (a) additions of  $0.2-2.0\,\mathrm{wt.\%}$  Bi $_2\mathrm{O_3}$  onto GDC submicronized powders all of them promoted densification of this ceramic electrolyte achieving almost theoretically dense bodies ( $\geq 99.8\%$ ), when GDC samples containing  $1.0\,\mathrm{wt.\%}$  Bi $_2\mathrm{O_3}$  were sintered at  $1400\,^\circ\mathrm{C}$  for 4 h, i.e. almost  $200\,^\circ\mathrm{C}$  lower than for undoped-GDC samples, (b) the extremely improved densification rate was believed to take place by a liquid phase-assisting mechanism, (c) the solubility limit of Bi $_2\mathrm{O_3}$  in the GDC structure was about  $0.8\,\mathrm{wt.\%}$  in the temperature range of  $1200-1400\,^\circ\mathrm{C}$ , and (d) Bi $_2\mathrm{O_3}$  additions retarded or at least do not promotes grain growth in doped-GDC samples sintered up to or below  $1350-1400\,^\circ\mathrm{C}$ , which was assumed to be due to a poor wetting properties of the formed liquid phase.

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